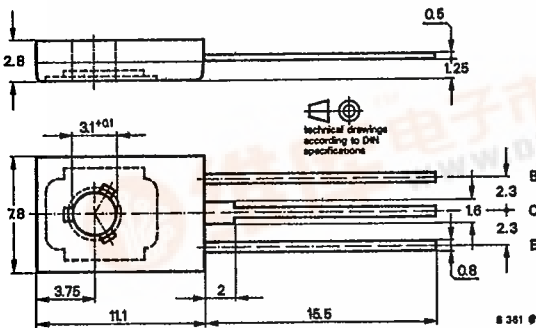


Silicon NPN Planar Power Transistors

Applications: General at high supply voltages

Features:

- High reverse voltage
- Power dissipation 17.5 W

Dimensions in mm

Collector connected with metallic surface

Standard plastic case
 12 A 3 DIN 41 869
 JEDEC TO 126 (SOT 32)
 Weight max. 0.8 g

Accessories

Isolating washer No. 119880

Washer 3.2 DIN 125A

Absolute maximum ratings

		BD 127	BD 128	BD 129	
Collector-base voltage	V_{CBO}	300	350	400	V
Collector-emitter voltage	V_{CEO}	250	300	350	V
Emitter-base voltage	V_{EBO}		5		V
Collector current	I_C		500		mA
Total power dissipation $T_{case} \leq 45^\circ C$	P_{tot}		17.5		W
Junction temperature	T_J		150		$^\circ C$
Storage temperature range	T_{stg}		-55 ... +150		$^\circ C$
Tightening torque	$M_A^{1)}$		70		N cm

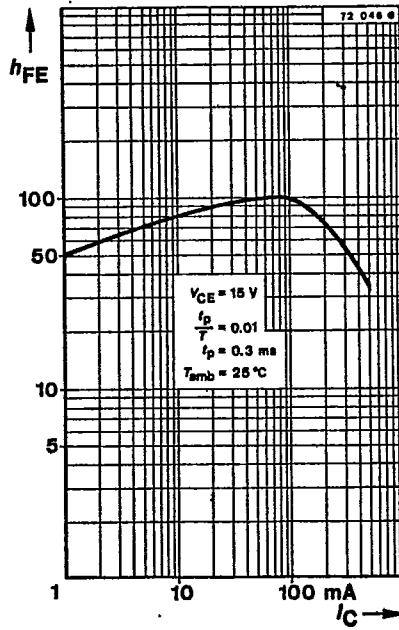
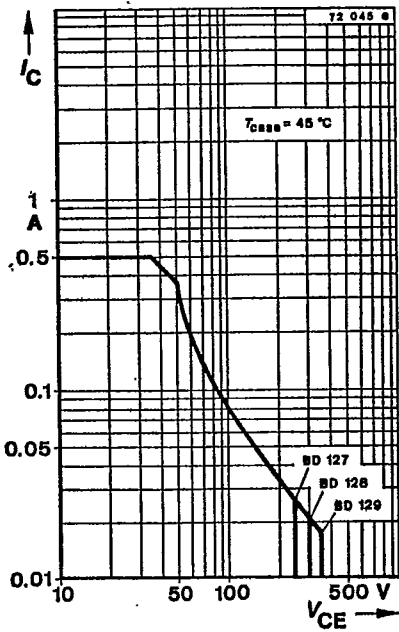
Maximum thermal resistance

Junction case	R_{thJC}		6		K/W
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1) with screw M3 and washer 3.2 DIN 125A

T-33-07

Characteristics	Min.	Typ.	Max.
$T_{amb} = 25^\circ\text{C}$, unless otherwise specified			
Collector cut-off current			
$V_{CB} = 150\text{ V}$			50 nA
$V_{CB} = 150\text{ V}, T_{amb} = 150^\circ\text{C}$			100 μA
Collector-base breakdown voltage			
$I_C = 1\ \mu\text{A}$			
BD 127	$V_{(BR)CBO}$	300	V
BD 128	$V_{(BR)CBO}$	350	V
BD 129	$V_{(BR)CBO}$	400	V
Collector-emitter breakdown voltage			
$I_C = 1\ \text{mA}$			
BD 127	$V_{(BR)CEO}^{1)}$	250	V
BD 128	$V_{(BR)CEO}^{1)}$	300	V
BD 129	$V_{(BR)CEO}^{1)}$	350	V
Emitter-base breakdown voltage			
$I_E = 1\ \mu\text{A}$	$V_{(BR)EBO}$	5	V
DC forward current transfer ratio			
$V_{CE} = 15\text{ V}, I_C = 1\ \text{mA}$	$h_{FE}^{1)}$	50	
$V_{CE} = 15\text{ V}, I_C = 50\ \text{mA}$	$h_{FE}^{1)}$	30	



¹⁾ $t_p = 0.01, t_p = 0.3\ \text{ms}$